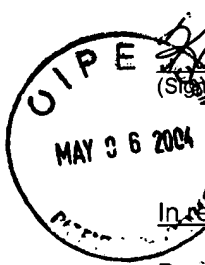


I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to : Commissioner of Patents and Trademarks, p. o. Box 1450, ALEXANDRIA, VA 22313-1450, on May 04, 2004. The applicant and/or attorney requests the date of deposit as the filing date. Depositor: Karen Cing-Mars

 Karen Cing-Mars 5/4/04
(Signature & date)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of _____ : May 04, 2004
Bruce B. Doris, et al. : Group Art Unit: Not yet assigned
Serial No.:10/709,314 Examiner: Not yet assigned
Filed: 4/28/04 : International Business Machines Corporation
2070 Route 52
Hopewell Junction, NY 12533

TITLE: Method for Forming Narrow Gate Structures on Sidewalls of a Lithographically Defined Sacrificial Material

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the non-US patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or non-pertinency of the art, that better art than that listed is not available, or that other art is not applicable.

No fee is believed to be due for this submission. If any fees are required, however, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 09-0458.

Respectfully submitted,
Bruce B. Doris, et al.

By Ira D. Blecker
Ira D. Blecker, Registration No. 29,894
Telephone No. 845-894-2580

INFORMATION DISCLOSURE CITATION*(Use several sheets if necessary)*

ATTY DOCKET NO.

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SERIAL NO.

10/709,314

BRUCE B. DORIS ET AL.

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GROUP

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

	3	Y. L. Zou, T. L. Alford, Y. Zeng, F. Deng, S. S. Lau, T. Laursen, A. I. Amali, and B. M. Ullrich; "Formation of Titanium Nitride by Annealing Ag/Ti Structures in Ammonia Ambient;" Journal of Applied Physics Vol. 82, (7).1; October 1997; pages 3321 - 3327.
	4	M. F. C. Willemsen, A. E. T. Kuiper, A. H. Reader, R. Hokke, and J. C. Barbour; "In Situ Investigation of TiN Formation of Top of TiSi2;" Journal of Vacuum Science Technology, B6(1), Jan/Feb 1988; pages 53 - 61

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	5	Y. Takahashi, H. Ishii, and J. Murota; "New Platinum Silicide Formation Method Using Reaction Between Platinum and Silane;" Journal of Applied Physics, 58 (8), 15 October 1985; pages 3190 - 3194.
	6	S. Hymes, Sp. P. Murarka, C. Shepard, and W. A. Lanford; "Passivation of Copper by Silicide Formation of Dilute Silane;" Journal of Applied Physics, 71 (9), 1 May 1992; pages 4623 - 4625

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FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	7	S. Humes, K.S. Kumar, S.P. Murarka, P. J. Ding, W. Wang, and W.A. Lanford; "Thermal Stability of Copper Silicide Passivation Layers in Copper-Based Multilevel Interconnects;" Journal of Applied Physics, Vo. 83, No. 9, April 15, 1998; pages 4507 - 4512
	8	L. H. Dubois and R.G. Nuzzo; "Reactivity of Intermetallic Thin Films Formed by the Surface Mediated Decomposition of Main Group Organometallic Compounds;" Journal of Vacuum Science Technologies, A2 (2), April - June 1984; pages 441 - 445.

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Docket Number (Optional)

FIS920040036US1

Application Number

10/709,314

Applicant(s)

Bruce B. Doris et al.

Filing Date

4/28/04

Group Art Unit

*EXAMINER
INITIAL

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

11

N. Matsui, K. Mashimo, A. Egami, A. Konishi, O. Okada, T. Tsukada; "Etching Characteristics of Magnetic Materials (Co, Fe, Ni) Using CO/NH3 Gas Plasma for Hardening Mask Etching;" Vacuum 66, 2002; pages 479 - 485

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